

ACJT810-10A

Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	0.5	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	2	kV

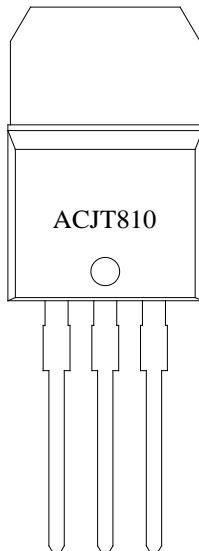
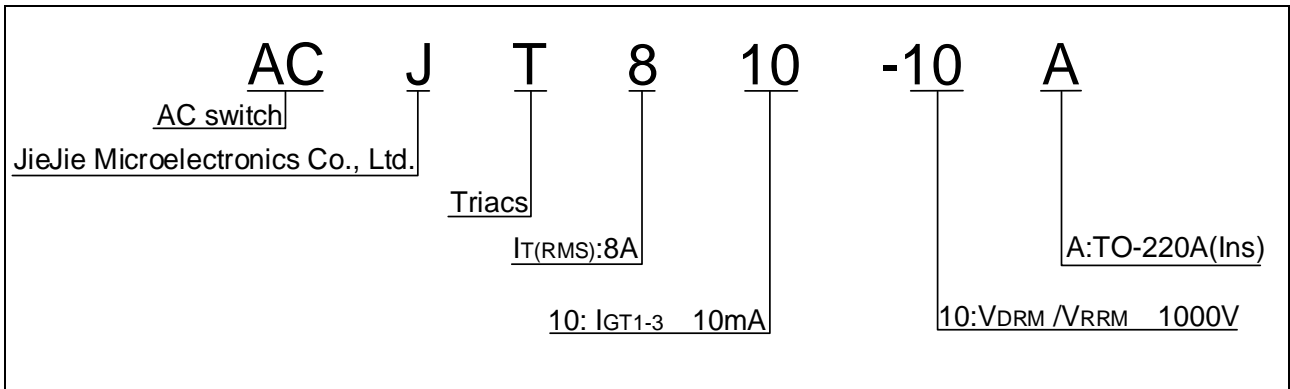


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



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